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November 2013

# FDP054N10

# N-Channel PowerTrench<sup>®</sup> MOSFET 100 V, 144 A, 5.5 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 4.6 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- · High Power and Current Handling Capability
- · RoHS Compliant

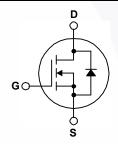
### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

## **Applications**

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter





#### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FDP054N10	Unit
V <sub>DSS</sub>	Drain to Source Voltage		100	V
V <sub>GSS</sub>	Gate to Source Voltage		±20	V
		- Continuous (T <sub>C</sub> = 25°C, Silicon Limited)	144	
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 100°C, Silicon Limited)	102	Α
		- Continuous (T <sub>C</sub> = 25°C, Package Limited)	120	
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	576	Α
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		1153	mJ
dv/dt	Peak Diode Avalanche Energ	gy (Note 3)	6	V/ns
n	Davier Dissipation	$(T_C = 25^{\circ}C)$	263	W
$P_{D}$	Power Dissipation	- Derate Above 25°C	1.75	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>I</sub>	Maximum Lead Temperature	e for Soldering, 1/8" from Case for 5 Seconds	300	οС

#### **Thermal Characteristics**

Symbol	Parameter FDP054N10		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.57	°C/W
$R_{\theta JA}$	hermal Resistance, Junction to Ambient, Max. 62.5		- 0/00

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP054N10	FDP054N10	TO-220	Tube	N/A	N/A	50 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	100	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	-	0.01	-	V/°C
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μА
DSS	Zero Gate voltage Drain Current	$V_{DS} = 100 \text{ V}, \ V_{GS} = 0 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	3.5	4.5	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 A	-	4.6	5.5	mΩ
9FS	Forward Transconductance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 A	-	192	-	S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 25 V V - 0 V	-	9985	13280	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1  MHz		935	1245	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-\	390	585	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 80 V, I <sub>D</sub> = 75 A,	-	156	203	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	-	53	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note 4)	-	48	-	nC

#### **Switching Characteristics**

	-						
t <sub>d(on)</sub>	Turn-On Delay Time	\/ F0\/   75 A		-	44	98	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 50 \text{ V, } I_{D} = 75 \text{ A,}$ $V_{GS} = 10 \text{ V, } R_{G} = 4.7 \Omega$		-	92	194	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	- VGS - 10 V, NG - 4.7 22		-	80	170	ns
t <sub>f</sub>	Turn-Off Fall Time	(	(Note 4)	- /	39	88	ns

# **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Dioc	Maximum Continuous Drain to Source Diode Forward Current		-	144	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	576	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A,	-	57	_	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	121	_	nC

#### Notes

- ${\bf 1:} \ \ {\bf Repetitive\ rating:\ pulse-width\ limited\ by\ maximum\ junction\ temperature.}$
- 2: L = 0.41 mH, I<sub>AS</sub> = 75 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.
- 3:  $I_{SD} \le 75$  A,  $di/dt \le 200$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J = 25^{\circ}C$ .
- 4: Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

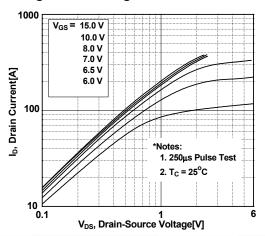


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

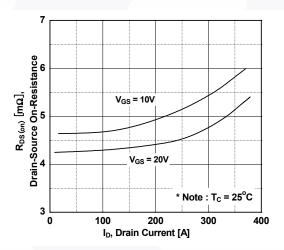


Figure 5. Capacitance Characteristics

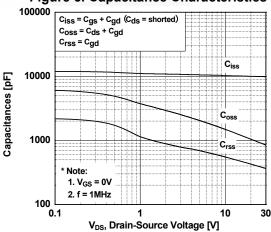


Figure 2. Transfer Characteristics

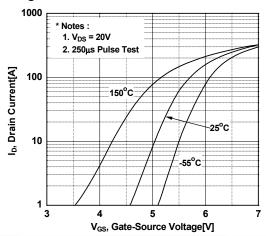


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

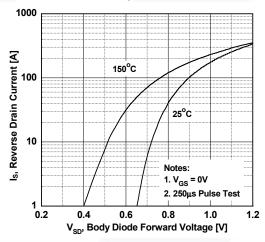
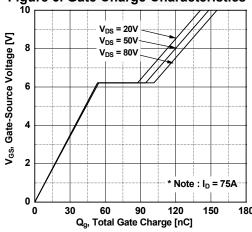


Figure 6. Gate Charge Characteristics



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

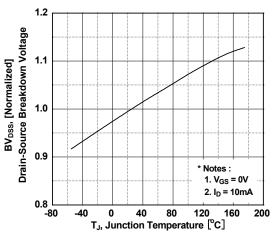


Figure 9. Maximum Safe Operating Area

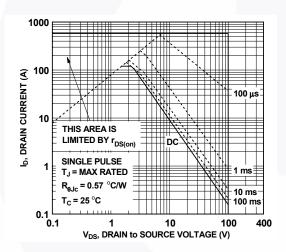


Figure 8. On-Resistance Variation vs. Temperature

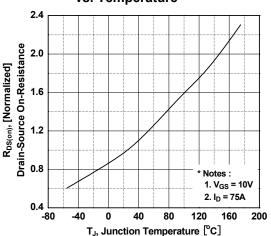


Figure 10. Maximum Drain Current vs. Case Temperature

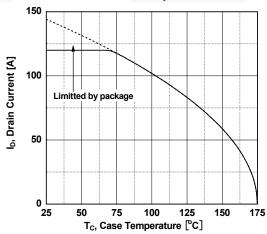
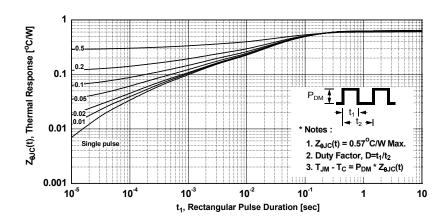


Figure 11. Transient Thermal Response Curve



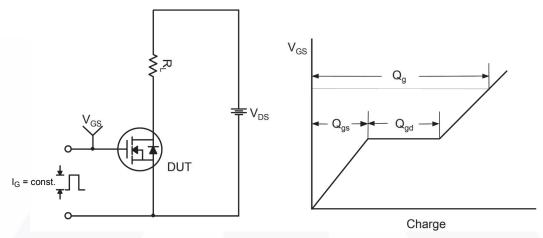


Figure 12. Gate Charge Test Circuit & Waveform

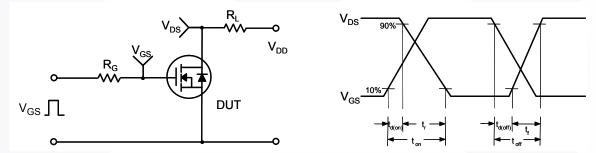


Figure 13. Resistive Switching Test Circuit & Waveforms

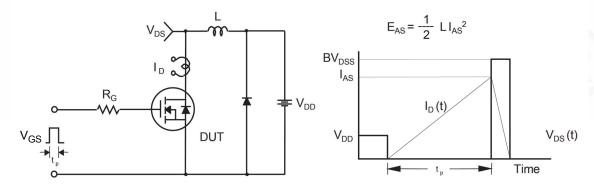


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

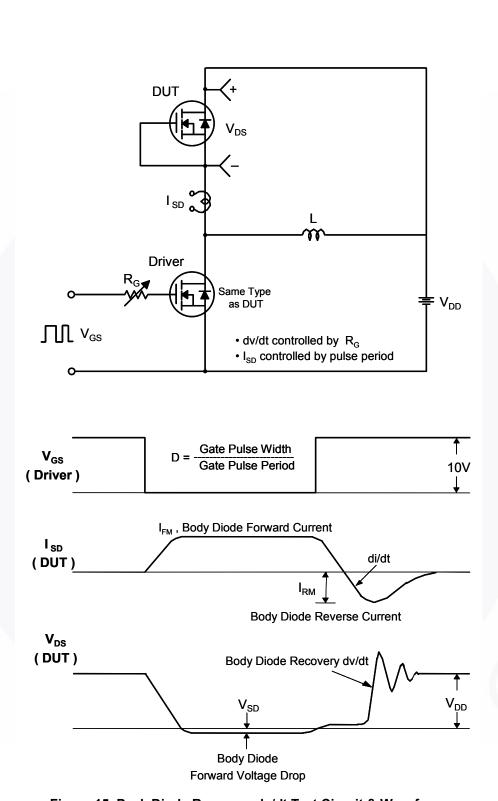


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

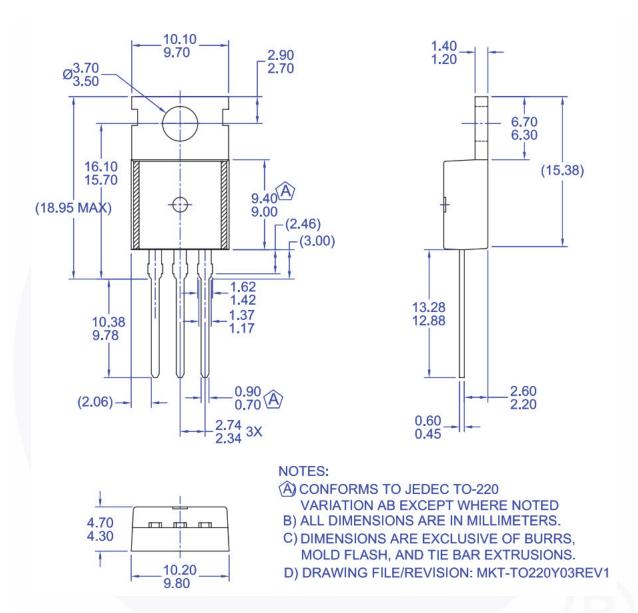


Figure 16. TO220, Molded, 3-Lead, Non Jedec Variation AB

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